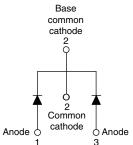


Vishay Semiconductors

Ultrafast Rectifier, 2 x 8 A FRED Pt®







PRODUCT SUMMARY					
Package	TO-220AB				
I _{F(AV)}	2 x 8 A				
V_{R}	200 V				
V _F at I _F	0.975 V				
t _{rr} typ.	See Recovery table				
T _J max.	175 °C				
Diode variation	Common cathode				

FEATURES

- · Ultrafast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified according to JEDEC-JESD47
- Halogen-free according to IEC 61249-2-21 definition (-N3 only)





RoHS

FREE Available

DESCRIPTION/APPLICATIONS

VS-MUR1620CTPbF is the state of the art ultrafast recovery rectifier specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Peak repetitive reverse voltage		V_{RRM}		200	V	
Average rectified forward comment	per leg			8.0		
Average rectified forward current	total device	I _{F(AV)}	Rated V _R , T _C = 150 °C	16	Α	
Non-repetitive peak surge current per leg		I _{FSM}		100	A	
Peak repetitive forward current per leg		I _{FM}	Rated V _R , square wave, 20 kHz, T _C = 150 °C	16		
Operating junction and storage temperatures		T _J , T _{Stg}		- 65 to 175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	TEST CONDITIONS MIN. TYP.		MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-		
Forward voltage	VF	I _F = 8 A	-	-	0.975	V	
	v _F	I _F = 8 A, T _J = 150 °C	-	-	0.895		
Reverse leakage current I _R		$V_R = V_R$ rated	-	-	5		
		$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	-	250	μΑ	
Junction capacitance	C _T	V _R = 200 V - 25 -		pF			
Series inductance	L _S	Measured lead to lead 5 mm from package body - 8.0 -		nΗ			



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time t _{rr}		$I_F = 1.0 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	-	35	
	t _{rr}	$I_F = 0.5 \text{ A}, I_R = 1.0 \text{ A}, I_{REC} = 0.25 \text{ A}$		-	-	25	
		T _J = 25 °C	I _F = 8 A	-	20	-	ns
		T _J = 125 °C		-	34	-	
Peak recovery current	I _{RRM}	T _J = 25 °C		-	1.7	-	Α
		IRRM	T _J = 125 °C	dI _F /dt = 200 A/µs V _R = 160 V	-	4.2	-
Reverse recovery charge	Q _{rr}	Q _{rr}	T _J = 25 °C		-	23	-
			T _J = 125 °C		-	75	-

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		- 65	-	175	°C
Thermal resistance, junction to case per leg	R _{thJC}		-	-	3.0	
Thermal resistance, junction to ambient per leg	R _{thJA}		-	-	50	°C/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-	
Woight			-	2.0	-	g
Weight			-	0.07	-	OZ.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-220AB		MUR1	620CT	•

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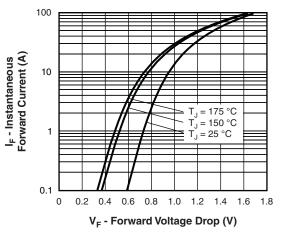


Fig. 1 - Typical Forward Voltage Drop Characteristics

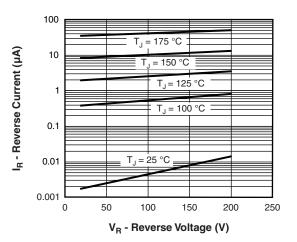


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

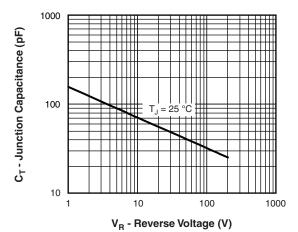


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

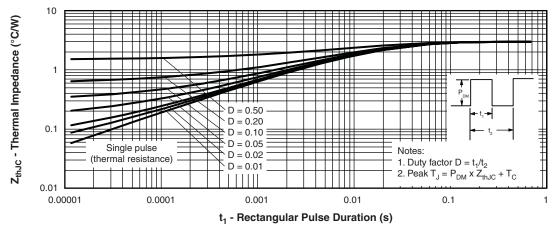
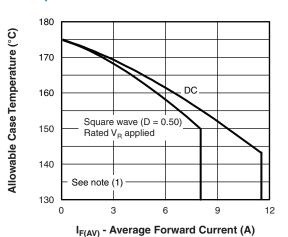


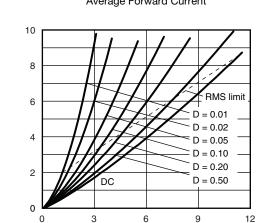
Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current



I_{F(AV)} - Average Forward Current (A) Fig. 6 - Forward Power Loss Characteristics

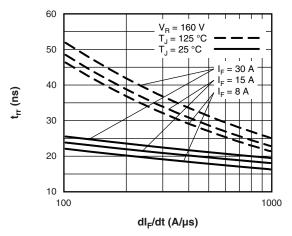


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

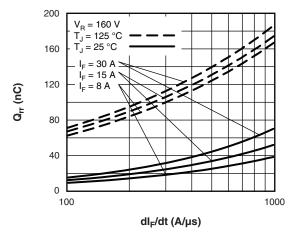


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

0

Average Power Loss (W)

 $^{(1)}$ Formula used: $T_{C} = T_{J}$ - (Pd + Pd_{REV}) x $R_{thJC};$ $Pd = Forward\ power\ loss = I_{F(AV)}\ x\ V_{FM}\ at\ (I_{F(AV)}/D)\ (see\ fig.\ 6);$ $Pd_{REV} = Inverse\ power\ loss = V_{R1}\ x\ I_R\ (1\ -\ D);\ I_R\ at\ V_{R1} = Rated\ V_R$

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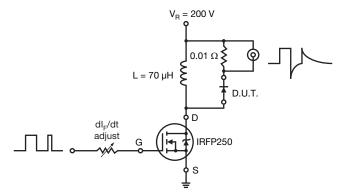
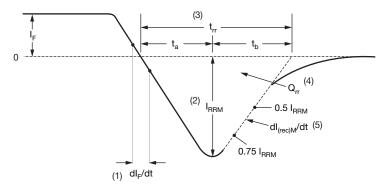


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

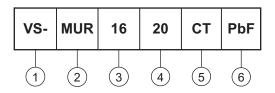
(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Ultrafast MUR series

3 - Current rating (16 = 16 A)

Voltage rating (20 = 200 V)

5 - CT = Center tap (dual)

- Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-N3 = Halogen-free, RoHS compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-MUR1620CTPbF	50	1000	Antistatic plastic tube		
VS-MUR1620CT-N3	50	1000	Antistatic plastic tube		

LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?95222</u>				
Dout moulding information	TO-220ABPbF	www.vishay.com/doc?95225		
Part marking information	TO-220AB-N3	www.vishay.com/doc?95028		



Legal Disclaimer Notice

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Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

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